

**REMARKS***Claim Rejections Under 35 U.S.C. § 112*

Claims 1-15 were rejected under 35 U.S.C. §112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claims 1 and 7 have been amended to overcome the rejection under 35 U.S.C. § 112, second paragraph. The expression “on the silicon substrate” was replaced with “in the silicon substrate” in both claims.

Applicant is unclear as to which claims have been examined with the present Office Action. The Office Action Summary page states that claims 1 – 10 are pending, the result of a response to the restriction requirement that was mailed September 9, 2004. However, the rejection under 35 U.S.C. § 112 appears to have examined claims 1 – 15. Applicant is proceeding under the assumption that this is a typographical error.

New claims 25 – 34 have been added to more thoroughly claim the subject matter of the present invention. New claim 25 is based on the subject matter of claim 7 except for claiming a low-trap-density dielectric material to substantially fill the trench as described in the specification at paragraph 21.

**CONCLUSION**

For the above-cited reasons, Applicant respectfully requests that the Examiner allow the claims of the present application. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211. No new matter has been added and no additional fee is required by this amendment and response.

Respectfully submitted,

Date: \_\_\_\_\_

1/12/05

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